ABSTRACT

With respect to a photoelectric conversion device comprising a semiconductor electrode composed of semiconductor fine particles and a metal film to be an opposite electrode, a polyethylene dioxythiophene (PEDOT)/polystyrenesulfonic acid (PSS) film is formed by spin coating on a transparent electrode of a metal oxide such as ITO to remarkably improve the adhesion property of the metal film to the metal oxide film and the pollution by the different type metal of the metal film to be the opposite electrode can be prevented in the photoelectric conversion device.

Further, a semiconductor electrode composed of semiconductor fine particles can be formed well on the metal oxide film by low temperature process while elution of the metal oxide film is prevented to obtain the photoelectric conversion device.